

4M-BIT CMOS FAST SRAM

512K-WORD BY 8-BIT

Description

The μ PD434008AL is a high speed, low power, 4,194,304 bits (524,288 words by 8 bits) CMOS static RAM.

Operating supply voltage is $3.3\text{ V} \pm 0.3\text{ V}$.

The μ PD434008AL is packaged in 36-pin plastic SOJ.

Features

- 524,288 words by 8 bits organization
- Fast access time : 15, 17, 20 ns (MAX.)
- Output Enable input for easy application
- Single +3.3 V power supply

Ordering Information

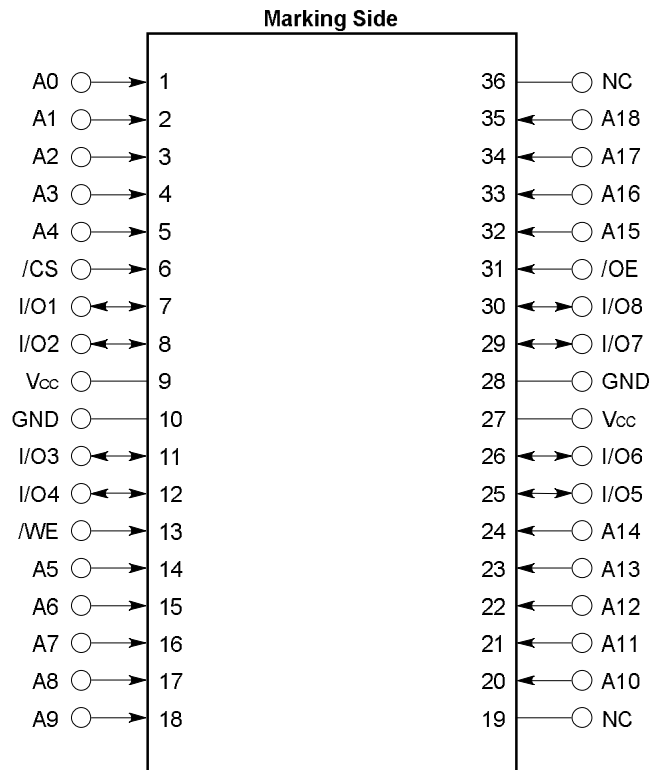
Part number	Package	Access time ns (MAX.)	Supply current mA (MAX.)	
			At operating	At standby
μ PD434008ALLE-A15	36-pin plastic SOJ (10.16 mm (400))	15	150	5
μ PD434008ALLE-A17		17	140	
μ PD434008ALLE-A20		20	130	

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

Pin Configuration

/xxx indicates active low signal.

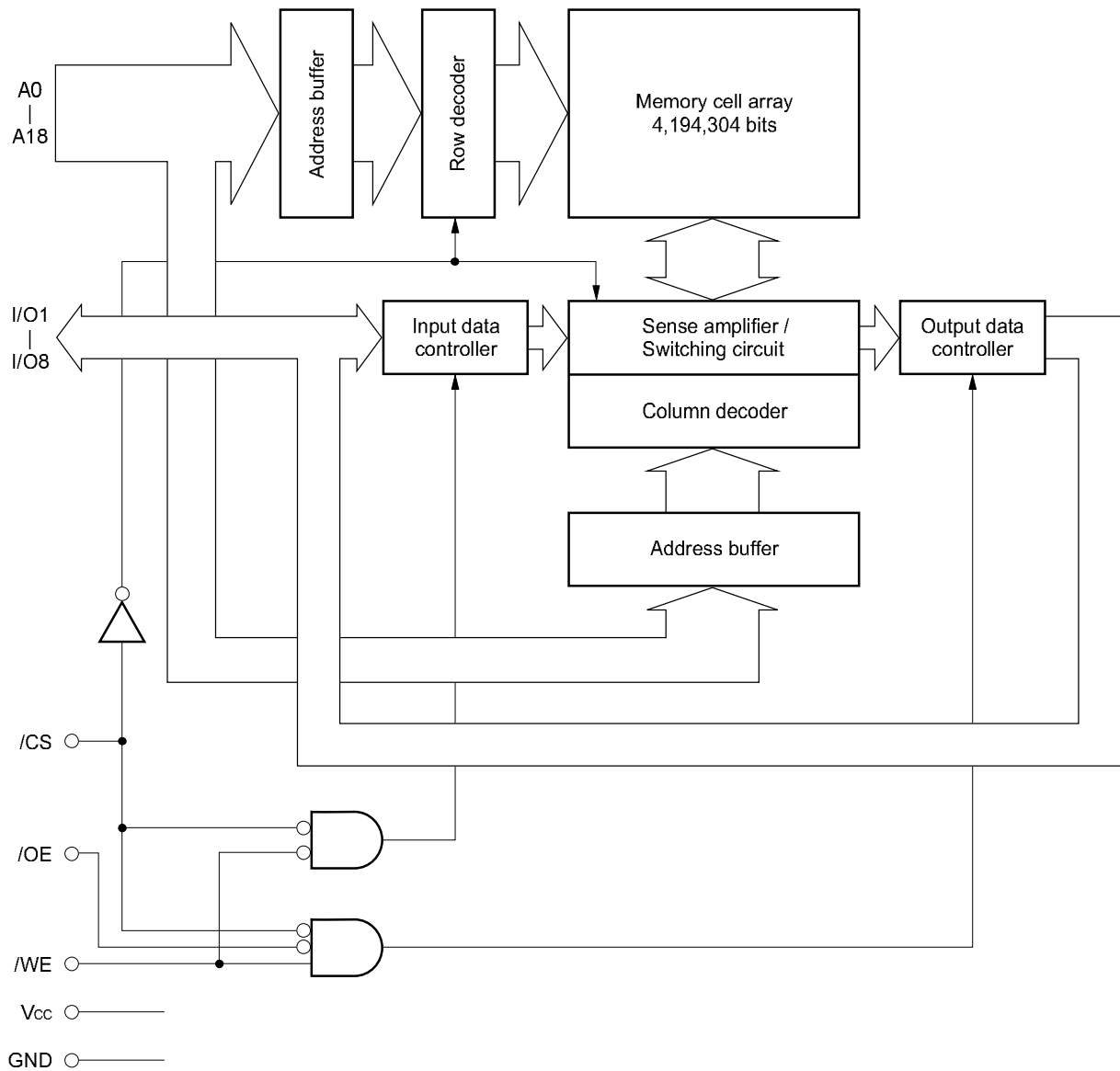
36-pin plastic SOJ (10.16 mm (400))



- A0 to A18 : Address Inputs
- I/O1 to I/O8 : Data Inputs / Outputs
- /CS : Chip Select
- /WE : Write Enable
- /OE : Output Enable
- Vcc : Power supply
- GND : Ground
- NC : No connection

Remark Refer to **Package Drawing** for the 1-pin index mark.

Block Diagram



Truth Table

/CS	/OE	/WE	Mode	I/O	Supply current
H	×	×	Not selected	High-Z	I_{SB}
L	L	H	Read	D_{OUT}	I_{CC}
L	×	L	Write	D_{IN}	
L	H	H	Output disable	High-Z	

Remark ×: Don't care

Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V _{CC}		-0.5 ^{Note} to +4.6	V
Input / Output voltage	V _I		-0.5 ^{Note} to +4.6	V
Operating ambient temperature	T _A		0 to 70	°C
Storage temperature	T _{stg}		-55 to +125	°C

Note -2.0 V (MIN.) (pulse width : 2 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{CC}		3.0	3.3	3.6	V
High level input voltage	V _{IH}		2.2		V _{CC} +0.3	V
Low level input voltage	V _{IL}		-0.3 ^{Note}		+0.8	V
Operating ambient temperature	T _A		0		70	°C

Note -2.0 V (MIN.) (pulse width : 2 ns)

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input leakage current	I _{LI}	V _{IN} = 0 V to V _{CC}	-2		+2	μA
Output leakage current	I _{LO}	V _{I/O} = 0 V to V _{CC} , /CS = V _{IH} or /OE = V _{IH} or /WE = V _{IL}	-2		+2	μA
Operating supply current	I _{CC}	/CS = V _{IL} , I _{I/O} = 0 mA, Minimum cycle time	Cycle time : 15 ns		150	mA
			Cycle time : 17 ns		140	
			Cycle time : 20 ns		130	
Standby supply current	I _{SB}	/CS = V _{IH} , V _{IN} = V _{IH} or V _{IL}			50	mA
	I _{SB1}	/CS ≥ V _{CC} - 0.2 V, V _{IN} ≤ 0.2 V or V _{IN} ≥ V _{CC} - 0.2 V			5	
High level output voltage	V _{OH}	I _{OH} = -4.0 mA	2.4			V
Low level output voltage	V _{OL}	I _{OL} = +8.0 mA			0.4	V

Remark V_{IN} : Input voltage
 V_{I/O} : Input / Output voltage

Capacitance (T_A = 25 °C, f = 1 MHz)

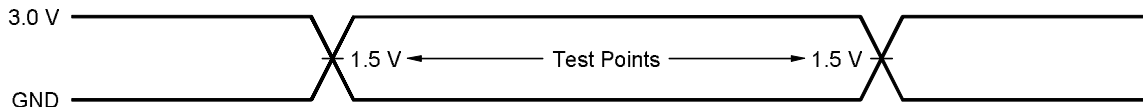
Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	C _{IN}	V _{IN} = 0 V			6	pF
Input / Output capacitance	C _{I/O}	V _{I/O} = 0 V			10	pF

Remarks 1. V_{IN} : Input voltage
 V_{I/O} : Input / Output voltage
 2. These parameters are periodically sampled and not 100% tested.

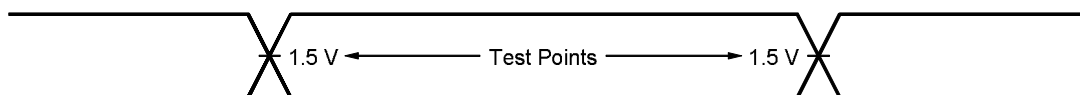
AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

AC Test Conditions

Input Waveform (Rise and Fall Time ≤ 3 ns)



Output Waveform



Output Load

AC characteristics directed with the note should be measured with the output load shown in **Figure 1** or **Figure 2**.

Figure 1

(for t_{AA} , t_{ACS} , t_{OE} , t_{OH})

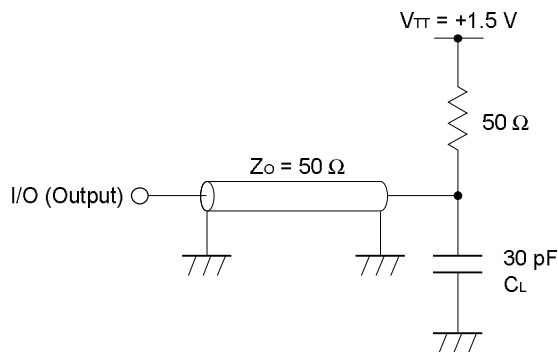
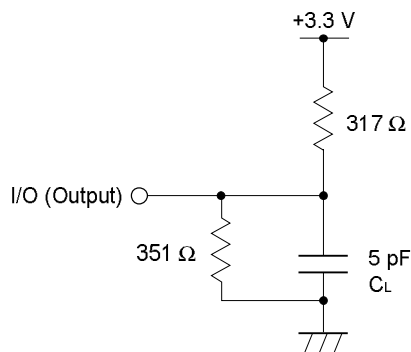


Figure 2

(for t_{CLZ} , t_{OLZ} , t_{CHZ} , t_{OHZ} , t_{WHZ} , t_{OW})



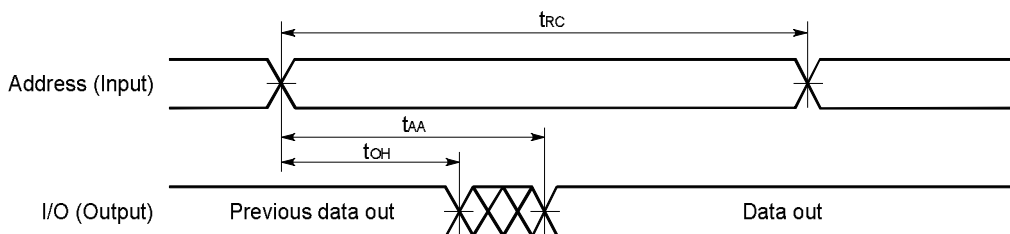
Remark C_L includes capacitances of the probe and jig, and stray capacitances.

Read Cycle

Parameter	Symbol	-A15		-A17		-A20		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t_{RC}	15		17		20		ns	
Address access time	t_{AA}		15		17		20	ns	1
/CS access time	t_{ACS}		15		17		20	ns	
/OE access time	t_{OE}		7		8		10	ns	
Output hold from address change	t_{OH}	3		3		3		ns	
/CS to output in low impedance	t_{CLZ}	3		3		3		ns	2, 3
/OE to output in low impedance	t_{OLZ}	0		0		0		ns	
/CS to output in high impedance	t_{CHZ}		7		8		8	ns	
/OE to output hold in high impedance	t_{OHZ}		7		8		8	ns	

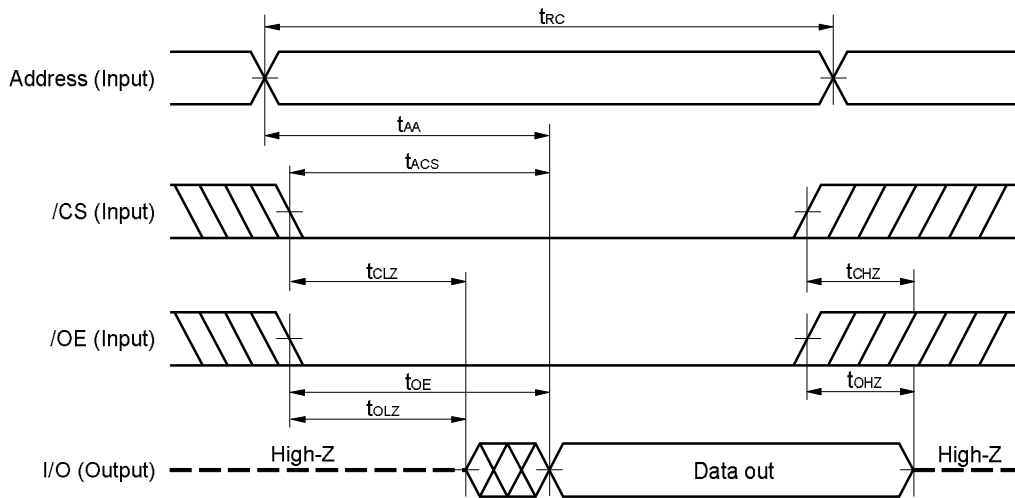
- Notes**
1. See the output load shown in **Figure 1**.
 2. Transition is measured at ± 200 mV from steady-state voltage with the output load shown in **Figure 2**.
 3. These parameters are periodically sampled and not 100% tested.

Read Cycle Timing Chart 1 (Address Access)



- Remarks**
1. In read cycle, /WE should be fixed to high level.
 2. /CS = /OE = V_{IL}

Read Cycle Timing Chart 2 (/CS Access)



Caution Address valid prior to or coincident with /CS low level input.

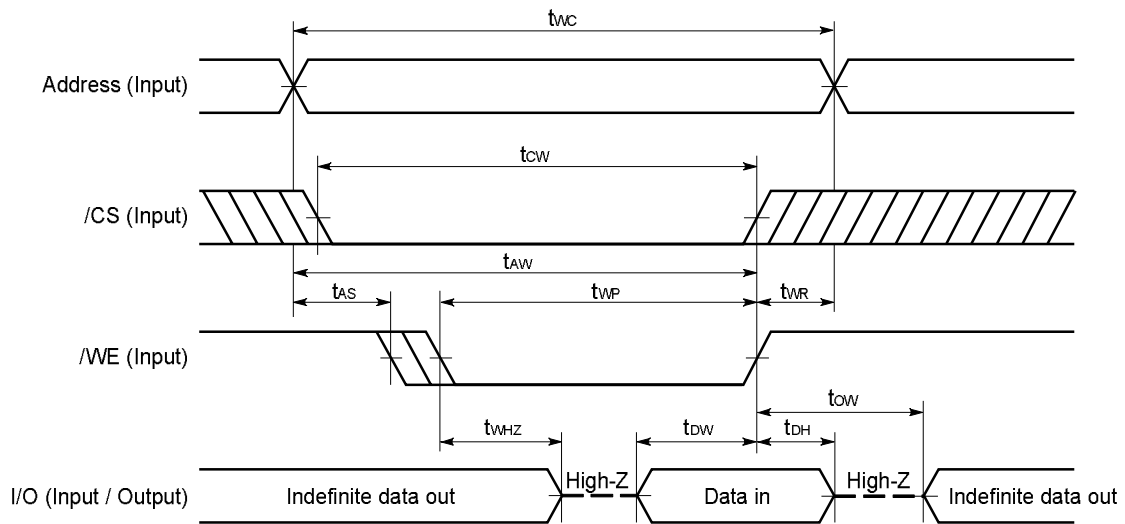
Remark In read cycle, /WE should be fixed to high level.

Write Cycle

Parameter	Symbol	-A15		-A17		-A20		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	t_{wc}	15		17		20		ns	
/CS to end of write	t_{cw}	10		11		12		ns	
Address valid to end of write	t_{aw}	10		11		12		ns	
Write pulse width	t_{wp}	10		11		12		ns	
Data valid to end of write	t_{dw}	7		8		9		ns	
Data hold time	t_{dh}	0		0		0		ns	
Address setup time	t_{as}	0		0		0		ns	
Write recovery time	t_{wr}	1		1		1		ns	
/WE to output in high impedance	t_{whz}		7		8		8	ns	1, 2
Output active from end of write	t_{ow}	3		3		3		ns	

- Notes**
1. Transition is measured at ± 200 mV from steady-state voltage with the output load shown in **Figure 2**.
 2. These parameters are periodically sampled and not 100% tested.

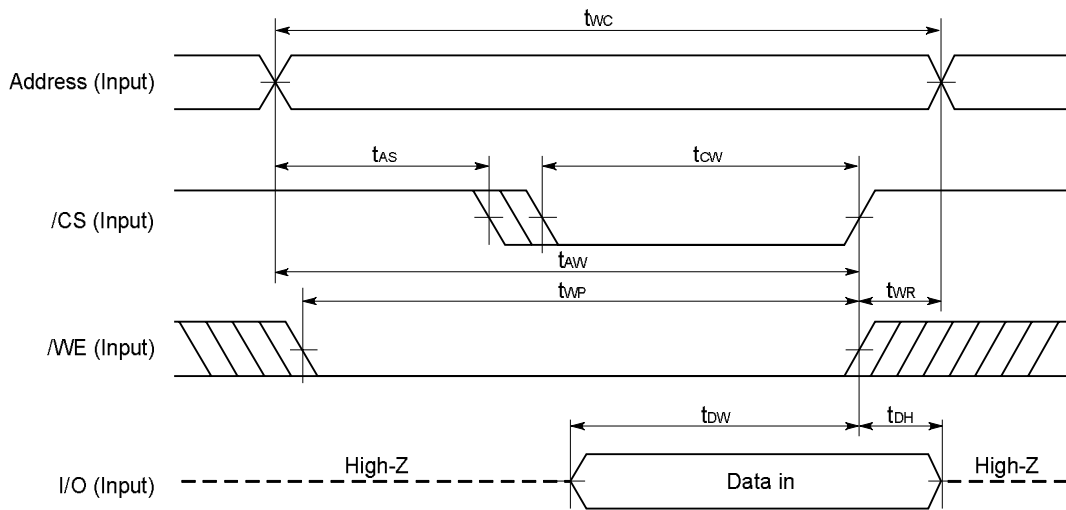
Write Cycle Timing Chart 1 (/WE Controlled)



Caution /CS or /WE should be fixed to high level during address transition.

- Remarks**
1. Write operation is done during the overlap time of a low level /CS and a low level /WE.
 2. During t_{whz} , I/O pins are in the output state, therefore the input signals must not be applied to the output.
 3. When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.

Write Cycle Timing Chart 2 (/CS Controlled)

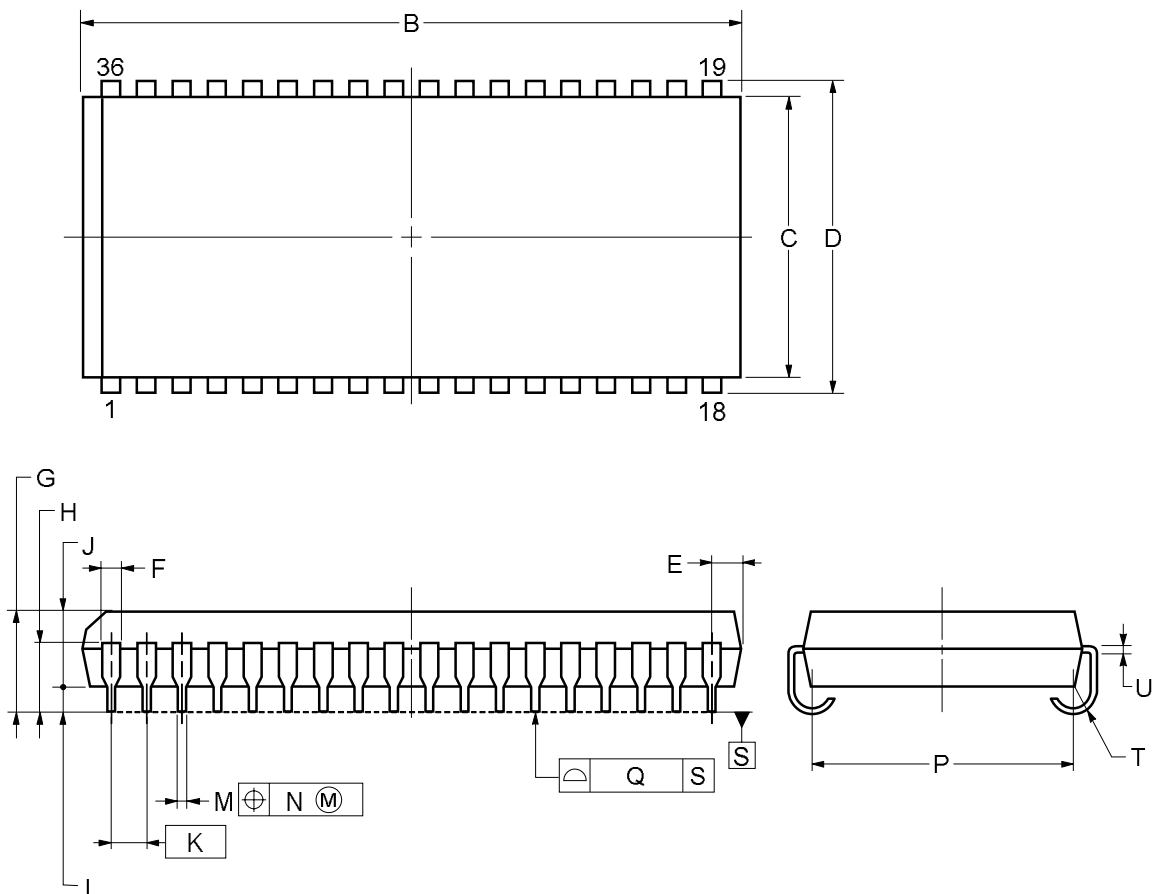


Caution $\overline{\text{CS}}$ or $\overline{\text{WE}}$ should be fixed to high level during address transition.

Remark Write operation is done during the overlap time of a low level $\overline{\text{CS}}$ and a low level $\overline{\text{WE}}$.

Package Drawing

36-PIN PLASTIC SOJ (10.16mm (400))



NOTE

Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
B	23.6±0.20
C	10.16±0.1
D	11.18±0.2
E	1.005±0.1
F	0.74
G	3.5±0.2
H	2.545±0.2
I	0.8 MIN.
J	2.6
K	1.27 (T.P.)
M	0.42 ^{+0.08} _{-0.07}
N	0.12
P	9.4±0.20
Q	0.1
T	R 0.85
U	0.22 ^{+0.08} _{-0.07}

P36LE-400A-2

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD434008AL.

Type of Surface Mount Device

μ PD434008ALLE : 36-pin plastic SOJ (10.16 mm (400))

Revision History

Edition/ Date	Page		Type of revision	Location	Description (Previous edition → This edition)
	This edition	Previous edition			
6th edition/ Oct. 2002	p.15	p.15	Modification	NOTES FOR CMOS DEVICES	②HANDLING OF UNUSED INPUT PINS FOR CMOS

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

★

② HANDLING OF THE APPLIED WAVEFORM OF INPUT PINS AND THE UNUSED INPUT PINS FOR CMOS

Note:

Input levels of CMOS devices must be fixed. CMOS devices behave differently than Bipolar or NMOS devices. For CMOS devices, through-current may flow inside and cause malfunction if a middle-level input due to noise etc. is applied to an input pin. Therefore, when the input waveform is fixed, and also when the waveform changes, it is recommended to use the CMOS device under AC test conditions. For unused input pins in particular, CMOS devices should not be operated in a state where nothing is connected, so input levels of CMOS devices must be fixed to high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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